

RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

DESCRIPTION

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $R_{DS(on)}$ and to ensure minimal power loss and heat dissipation.

FEATURES

- Low $R_{DS(on)}$ provides higher efficiency and extends battery life.
- Low thermal impedance copper leadframe SC-59 saves board space.
- Fast switching speed.
- High performance trench technology.

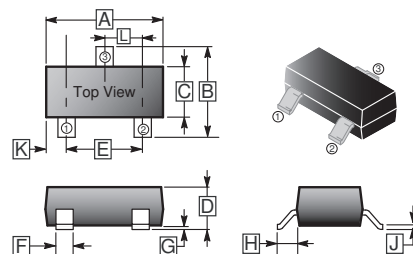
APPLICATION

DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

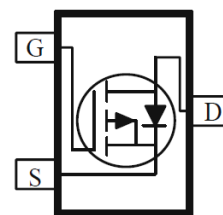
PACKAGE INFORMATION

Package	MPQ	Leader Size
SC-59	3K	7 inch

SC-59



REF.	Min.	Max.	REF.	Min.	Max.
A	2.70	3.10	G	0.10	REF.
B	2.25	3.00	H	0.40	REF.
C	1.30	1.70	J	0.10	0.20
D	1.00	1.40	K	0.45	0.55
E	1.70	2.30	L	0.85	1.15
F	0.35	0.50			



ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ¹	I_D	-3.4	A
		-2.6	
Pulsed Drain Current ²	I_{DM}	-20	A
Continuous Source Current (Diode Conduction) ¹	I_S	-1.6	A
Power Dissipation ¹	P_D	1.3	W
		0.8	
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55~150	$^\circ\text{C}$
Thermal Resistance Data			
Maximum Junction to Ambient ¹	$t \leq 10 \text{ sec}$	$R_{\theta JA}$	$^\circ\text{C} / \text{W}$
	Steady-State		

Notes:

1. Surface Mounted on 1" x 1" FR4 Board.
2. Pulse width limited by maximum junction temperature.

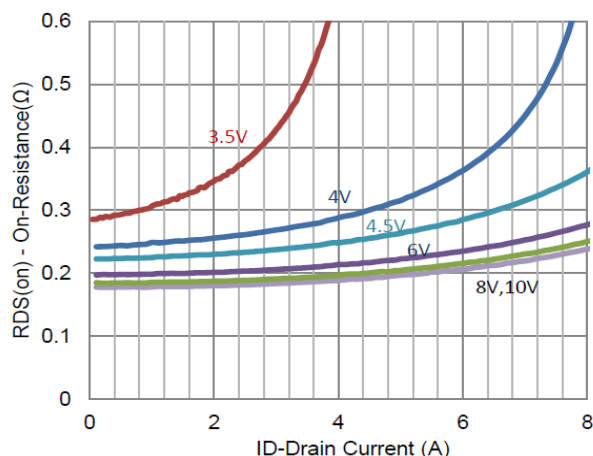
ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Static						
Gate-Threshold Voltage	$V_{GS(th)}$	-1	-	-	V	$V_{DS}=V_{GS}$, $I_D = -250\mu\text{A}$
Gate-Body Leakage	I_{GSS}	-	-	± 100	nA	$V_{DS}=0$, $V_{GS} = \pm 20\text{V}$
Zero Gate Voltage Drain Current	I_{DSS}	-	-	-1	μA	$V_{DS} = -48\text{V}$, $V_{GS}=0$
		-	-	-10		$V_{DS} = -48\text{V}$, $V_{GS}=0$, $T_J=55^\circ\text{C}$
On-State Drain Current ¹	$I_{D(ON)}$	-8	-	-	A	$V_{DS} = -5\text{V}$, $V_{GS} = -10\text{V}$
Drain-Source On-Resistance ¹	$R_{DS(ON)}$	-	-	210	m Ω	$V_{GS} = -10\text{V}$, $I_D = -2.7\text{A}$
		-	-	250		$V_{GS} = -4.5\text{V}$, $I_D = -2.2\text{A}$
Forward Transconductance ¹	g_{FS}	-	10	-	S	$V_{DS} = -15\text{V}$, $I_D = -2.7\text{A}$
Diode Forward Voltage	V_{SD}	-	-0.83	-	V	$I_S = -0.8\text{A}$, $V_{GS}=0$
Dynamic ²						
Total Gate Charge	Q_g	-	5	-	nC	$I_D = -2.7\text{A}$ $V_{DS} = -30\text{V}$ $V_{GS} = -4.5\text{V}$
Gate-Source Charge	Q_{gs}	-	2.2	-		
Gate-Drain Charge	Q_{gd}	-	2.3	-		
Turn-On Delay Time	$T_{d(ON)}$	-	7	-	nS	$I_D = -2.7\text{A}$, $V_{DS} = -30\text{V}$, $V_{GEN} = -10\text{V}$, $R_{GEN}=6\Omega$ $R_L=11.2\Omega$
Rise Time	T_r	-	5	-		
Turn-Off Delay Time	$T_{d(OFF)}$	-	23	-		
Fall Time	T_f	-	6	-		
Input Capacitance	C_{iss}	-	371	-	pF	$V_{DS} = -15\text{V}$ $V_{GS}=0$ $f=1\text{MHz}$
Output Capacitance	C_{oss}	-	31	-		
Reverse Transfer Capacitance	C_{rss}	-	26	-		

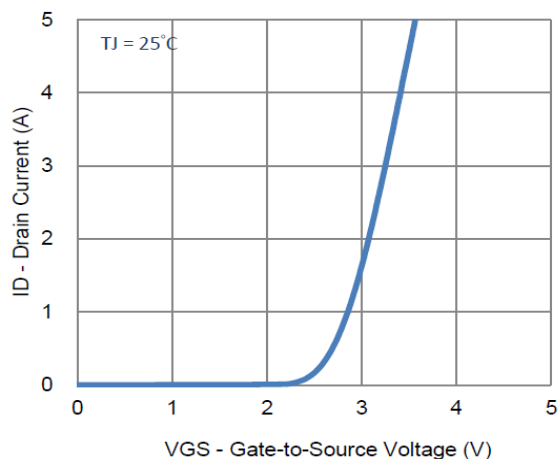
Notes:

1. Pulse test : $PW \leq 300 \mu\text{s}$ duty cycle $\leq 2\%$.
2. Guaranteed by design, not subject to production testing.

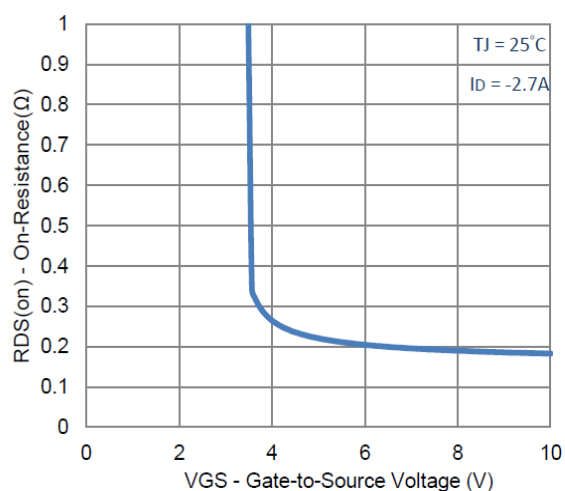
CHARACTERISTIC CURVE



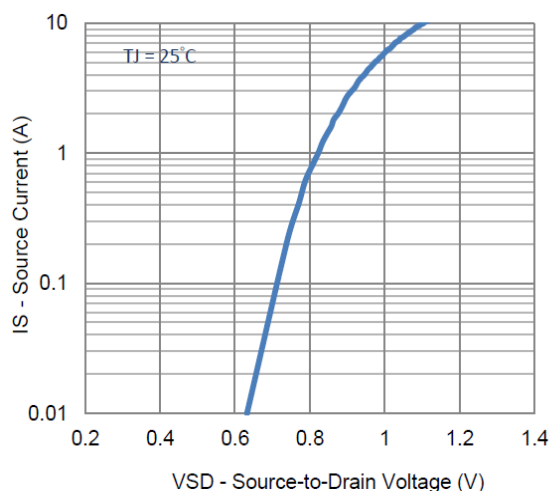
1. On-Resistance vs. Drain Current



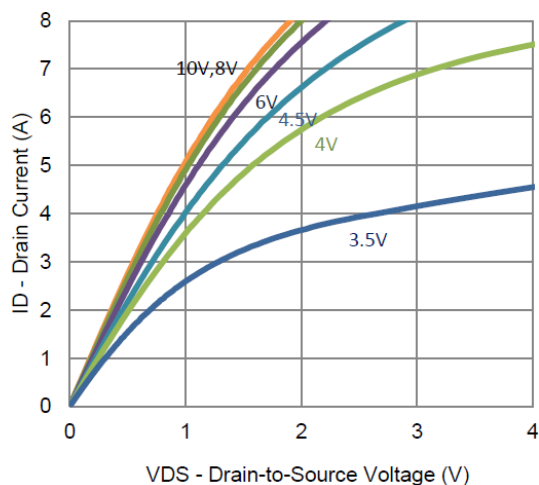
2. Transfer Characteristics



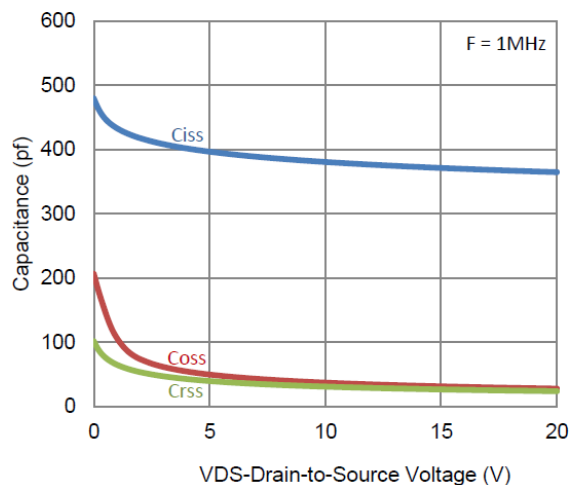
3. On-Resistance vs. Gate-to-Source Voltage



4. Drain-to-Source Forward Voltage



5. Output Characteristics



6. Capacitance

CHARACTERISTIC CURVE

